

# 1.2V Drive Nch MOSFET

## **RUM002N05**

#### Structure

Silicon N-channel MOSFET SOT-72

#### ● Features

- 1) High speed switing.
- 2) Small package(VMT3).
- 3)Ultra low voltage drive(1.2V drive).

## Application

Switching

Packaging specifications

Type	Package	Taping	
	Code	T2L	
	Basic ordering unit (pieces)	8000	
RUM002N0	0		

## ● Absolute maximum ratings (Ta = 25°C)

Param	Symbol	mbol Limits		
Drain-source voltage		$V_{DSS}$	50	V
Gate-source voltage		$V_{GSS}$	±8	V
Drain current	Continuous	$I_{D}$	±200	mA
	Pulsed	I <sub>DP</sub> *1	±800	mA
Source current	Continuous	I <sub>S</sub>	125	mA
(Body Diode)	Pulsed	I <sub>SP</sub> *1	800	mA
Power dissipation		P <sub>D</sub> *2	150	mW
Channel temperature		Tch	150	°C
Range of storage temperature		Tstg	-55 to +150	°C

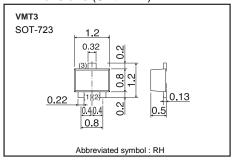
<sup>\*1</sup> Pw≤10µs, Duty cycle≤1%

#### ● Thermal resistance

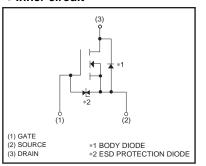
Parameter	Symbol	Limits	Unit
Channel to Ambient	Rth (ch-a)*	833	°C / W

<sup>\*</sup> Each terminal mounted on a recommended land.

## • Dimensions (Unit : mm)



#### • Inner circuit



<sup>\*2</sup> Each terminal mounted on a recommended land.

## ●Electrical characteristics (Ta = 25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Gate-source leakage	I <sub>GSS</sub>	1	-	±10	μA	$V_{GS}=\pm 8V, V_{DS}=0V$
Drain-source breakdown voltage	$V_{(BR)DSS}$	50	-	-	٧	I <sub>D</sub> =1mA, V <sub>GS</sub> =0V
Zero gate voltage drain current	I <sub>DSS</sub>	1	-	1	μA	$V_{DS}$ =50V, $V_{GS}$ =0V
Gate threshold voltage	V <sub>GS (th)</sub>	0.3	-	1.0	٧	$V_{DS}$ =10V, $I_{D}$ =1mA
		1	1.6	2.2	Ω	I <sub>D</sub> =200mA, V <sub>GS</sub> =4.5V
Static ducin course on state		1	1.7	2.4		I <sub>D</sub> =200mA, V <sub>GS</sub> =2.5V
Static drain-source on-state resistance	R <sub>DS (on)</sub> *	1	1.9	2.7		I <sub>D</sub> =100mA, V <sub>GS</sub> =1.8V
resistante		1	2.0	4.0		I <sub>D</sub> =40mA, V <sub>GS</sub> =1.5V
		1	2.4	7.2		I <sub>D</sub> =20mA, V <sub>GS</sub> =1.2V
Forward transfer admittance	I Y <sub>fs</sub> I*	0.4	-	-	S	I <sub>D</sub> =200mA, V <sub>DS</sub> =10V
Input capacitance	C <sub>iss</sub>	1	25	-	pF	V <sub>DS</sub> =10V
Output capacitance	C <sub>oss</sub>	1	6	-	pF	V <sub>GS</sub> =0V
Reverse transfer capacitance	C <sub>rss</sub>	-	3	-	pF	f=1MHz
Turn-on delay time	t <sub>d(on)</sub> *	1	4	-	ns	I <sub>D</sub> =100mA, V <sub>D</sub> =30V
Rise time	t <sub>r</sub> *	-	6	-	ns	V <sub>GS</sub> =4.5V
Turn-off delay time	t <sub>d(off)</sub> *	-	15	-	ns	$R_L=300\Omega$
Fall time	t <sub>f</sub> *	-	55	-	ns	$R_G=10\Omega$

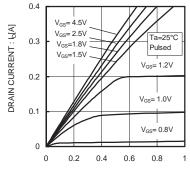
<sup>\*</sup>Pulsed

●Body diode characteristics (Source-Drain) (Ta = 25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Forward voltage	V <sub>SD</sub> *	-	-	1.2	V	I <sub>s</sub> =200mA, V <sub>GS</sub> =0V

<sup>\*</sup>Pulsed

#### •Electrical characteristic curves



DRAIN-SOURCE VOLTAGE :  $V_{DS}[V]$ Fig.1 Typical Output Characteristics( I )

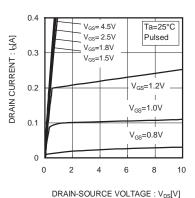
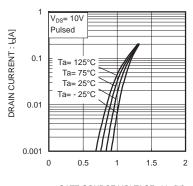


Fig.2 Typical Output Characteristics( II )



GATE-SOURCE VOLTAGE : V<sub>GS</sub>[V] Fig.3 Typical Transfer Characteristics

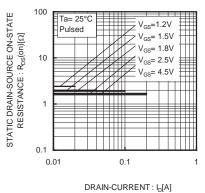


Fig.4 Static Drain-Source On-State Resistance vs. Drain Current( I )

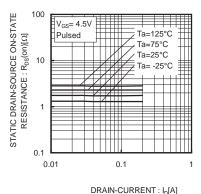


Fig.5 Static Drain-Source On-State Resistance vs. Drain Current( II )

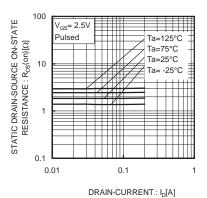


Fig.6 Static Drain-Source On-State Resistance vs. Drain Current( III )

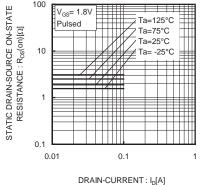


Fig.7 Static Drain-Source On-State
Resistance vs. Drain Current( IV )

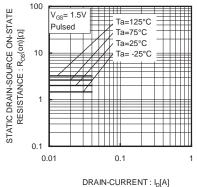


Fig.8 Static Drain-Source On-State
Resistance vs. Drain Current( V )

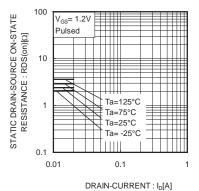
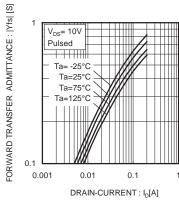


Fig.9 Static Drain-Source On-State
Resistance vs. Drain Current( VI )





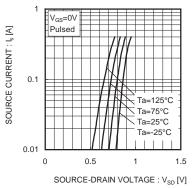


Fig.11 Reverse Drain Current vs. Sourse-Drain Voltage

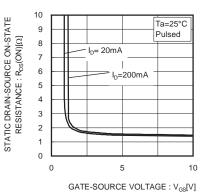
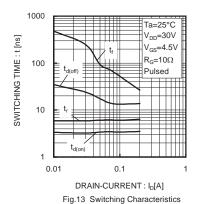
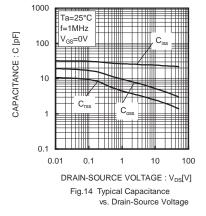


Fig.12 Static Drain-Source On-State
Resistance vs. Gate Source Voltage





#### ●Measurement circuits

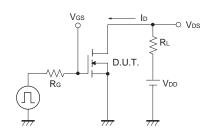


Fig.1-1 Switching time measurement circuit

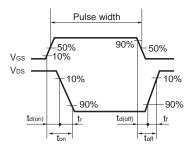


Fig.1-2 Switching waveforms

#### Notice

This product might cause chip aging and breakdown under the large electrified environment. Please consider to design ESD protection circuit.

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